IN THE SPECIFICATION:

Please replace the paragraph at page 8A, lns. 7-9 with the following amended paragraph:

FIG. 11 is a cross-sectional view at ~~B-B'~~ III-III' of FIG. 10(B) showing a cross section of the switching TFT, storage capacitance, current control TFT and organic EL element portion.

Please replace the paragraph at page 8A, lns. 13-14 with the following amended paragraph:

FIG. 12(B) is a cross sectional view of ~~A-A'~~ IV-IV' of FIG. 12(A) showing the structure of an EL display device.

Please replace the paragraph at page 8A, lns. 18-19 with the following amended paragraph:

FIG. 13(B) is a cross sectional view at ~~A-A'~~ V-V' of FIG. 13(A) showing the structure of an EL display device.

Please replace the paragraph at page 24, ln. 18 - page 25, ln. 5 with the following amended paragraph:

FIG. 6 (A) is a top plan view of the pixel matrix circuit 501 and the top plan view of nearly one pixel. FIG. 6 (B) is a top plan view of a CMOS circuit constituting the driving circuits 502, 503. FIG. 7 is a cross-sectional view of the active matrix substrate, and a cross-sectional view of the pixel matrix circuit 501 and the CMOS circuit. The cross-sectional view of the CMOS circuit corresponds to a cross-section along a chain line ~~X-X'~~ I-I' in FIG. 6 (A), and the cross-sectional view of the pixel matrix circuit 501 corresponds to a cross-section along a chain line ~~Y-Y'~~ Y-Y' in FIG. 6 (B).

Please replace the paragraph at page 31, ln. 21 - page 32, ln. 16 with the following amended paragraph:

Fig. 11 is a cross section taken along the line ~~B-B'~~ III-III' of Fig. 10(B), showing the cross section of the switching TFT 30, storage capacitance 32, current control TFT 31 and organic EL element portion. Over a substrate 40, base films 41, 42, gate insulating film 45, first interlayer insulating film 46, gate electrodes 47, 48, capacitance line 49, source and drain lines 18a, 19a, 51, 52, and second interlayer insulating film 50 are formed in the same way as in the example 1. Then, over these layers is formed a third interlayer insulating film 53 in a way similar to the second interlayer insulating film 50. A contact hole reaching the drain line 52 is formed, after which a pixel electrode 54 made of a transparent conductive film is formed. The organic EL element portion comprises the pixel electrode 54; an organic EL layer 55 overlying the pixel electrode and the third interlayer insulating film 53; and a first electrode 56 made of Mg-Ag compound and a second electrode 57 made of Al, formed over the organic EL layer 55. If a color filter, though not shown, is used, a color display is possible. By applying the active matrix substrate manufacturing method shown in the examples 1 to 10, the active matrix type organic EL display can be fabricated easily.

Please replace the paragraph at page 38, lns. 6-7 with the following amended paragraph:

Fig. 13A shows a top view of the EL module in this example and Fig. 13B shows a sectional view of ~~A-A'~~ V-V' of Fig. 13A.